

/ Descriptions

TO-251 N MOS N-CHANNEL MOSFET in a TO-251 Plastic Package.

/ Features

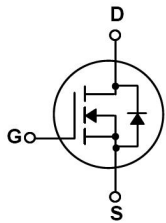
Low gate charge, low crss, fast switching, HF Product.

/ Applications

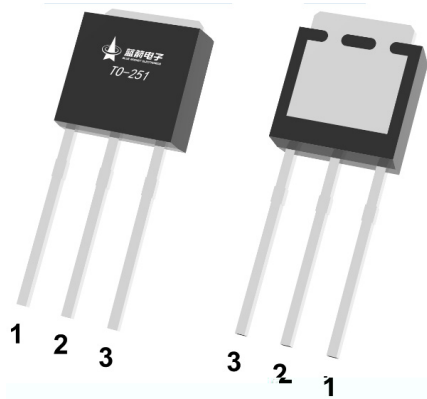
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

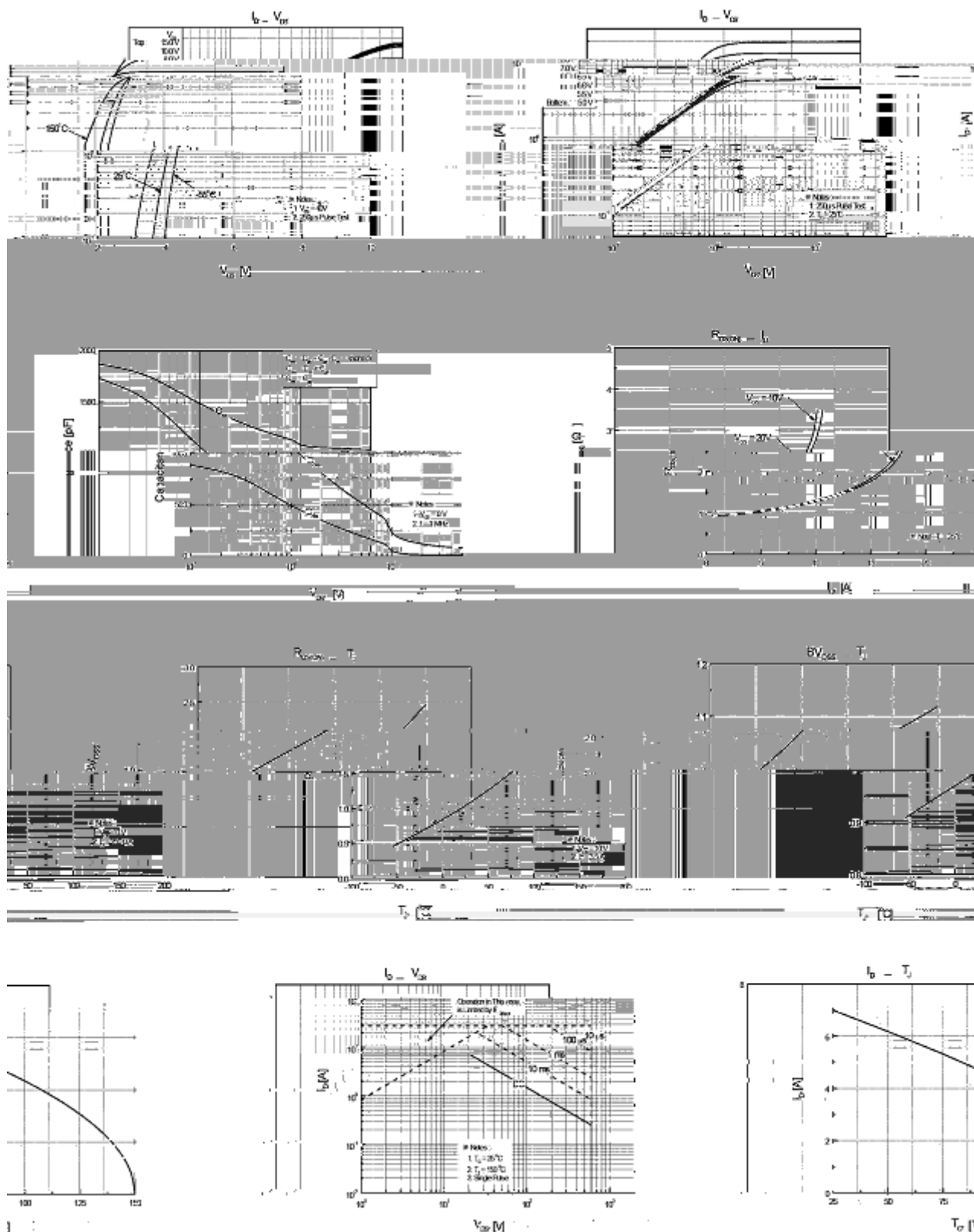
PIN 3 S

/ Marking

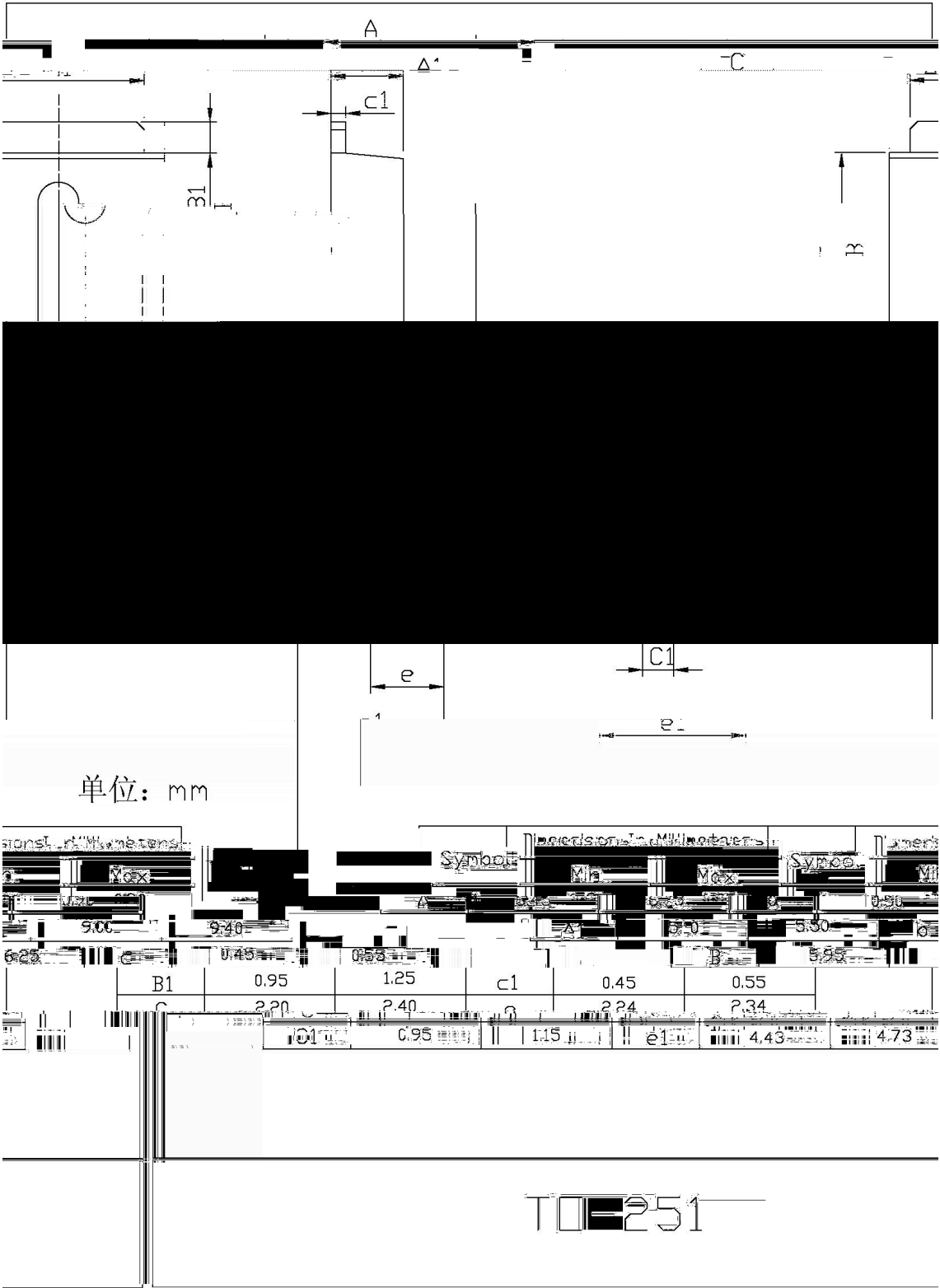
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	7.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	4.4	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	230	mJ
Repetitive Avalanche Energy	E_{AR}	14.7	mJ
Avalanche Current	I		

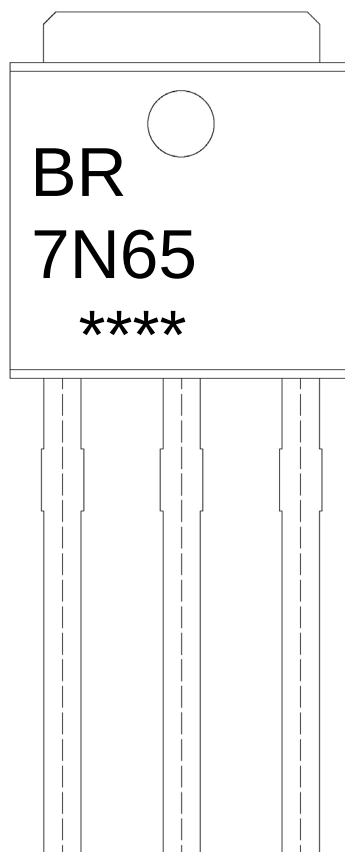
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

7N65

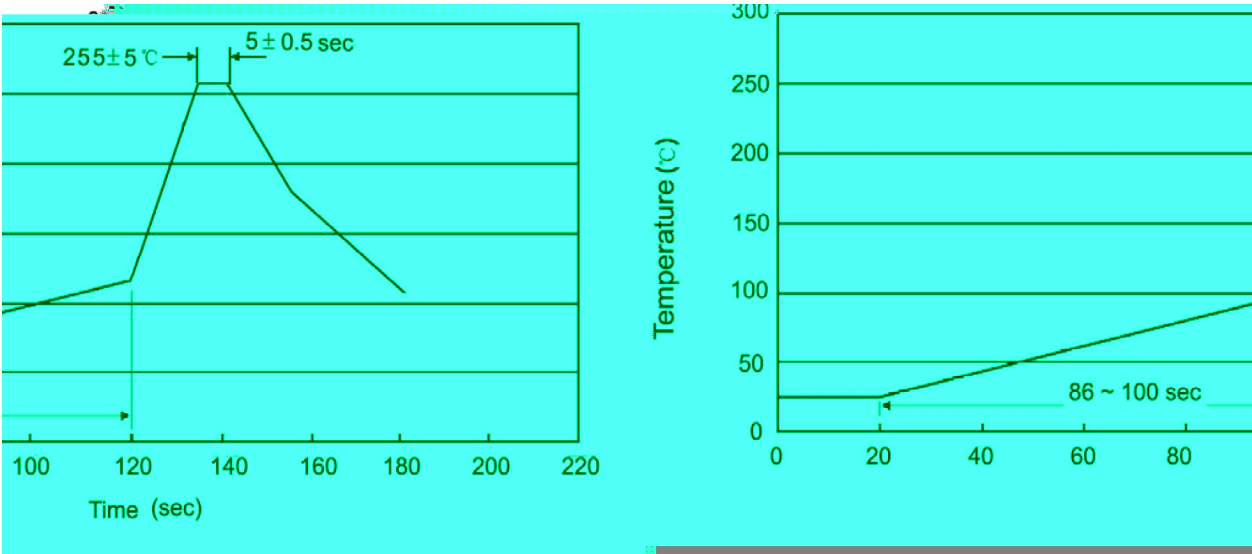
Note:

BR: Company Code

7N65: Product Type

****: Lot No. Code, code change with Lot No

() / Temperature Profile for Dip Soldering(Pb-Free)



- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10 /sec.
- Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5℃ Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit ㎜ mm ³)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-251	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension (unit ㎜ mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ Notices